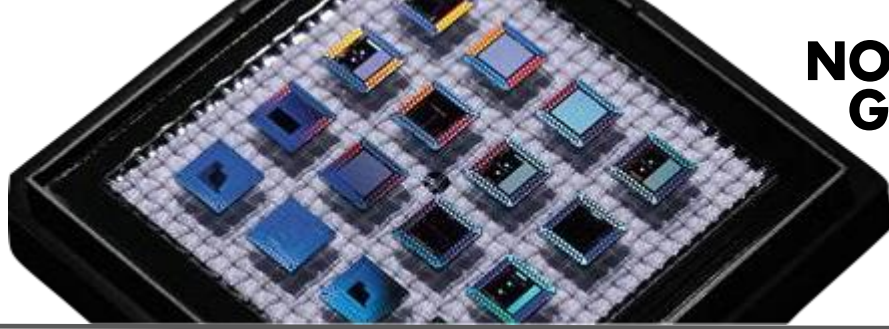
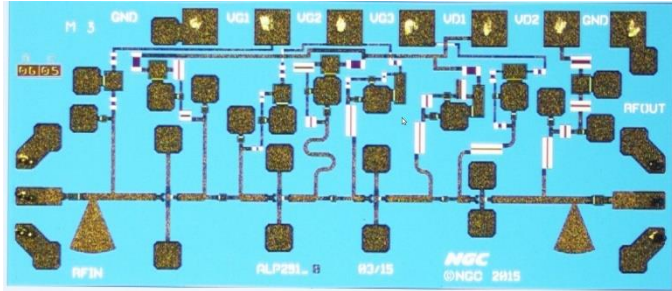


ALP291

71–86 GHz
Low Noise
Amplifier



Revision 2022-1



x=1.9 mm; y=0.85 mm

Product Description

The ALP291 is an E-band low noise amplifier MMIC fabricated in 0.1um InP HEMT. This part is ideally suited for communications. The MMIC operates from 71 to 86 GHz and provides greater than 24 dB of gain with an average noise figure of 2.7 dB. The small die size allows for extremely compact packaging. To ensure rugged and reliable operation, HEMT devices are fully passivated. Both bond pad and backside metallization are Ti/Au, which is compatible with conventional die attach, thermocompression and thermosonic wire bonding assembly techniques

Applications

- Point-to-Point Digital Radios
- Point-to-Multipoint Digital Radios
- SatCom Terminals

Product Features

- Linear gain: 24 - 25 dB, typical
- Noise Figure: 2.5 – 2.9 dB, typical
- Average NF (71-86 GHz): 2.7 dB, typical
- P1dB : 3 dBm (Est.)
- Microstrip Topology MMIC, In-line Input & Output
- 0.1 um InP HEMT Process
- 3 mil substrate
- DC Power: 25 mW
- Die Size 1.6 sq. mm

Export Information

ECCN: 5A991.h

HTS (Schedule B) code: 8542.33.0000

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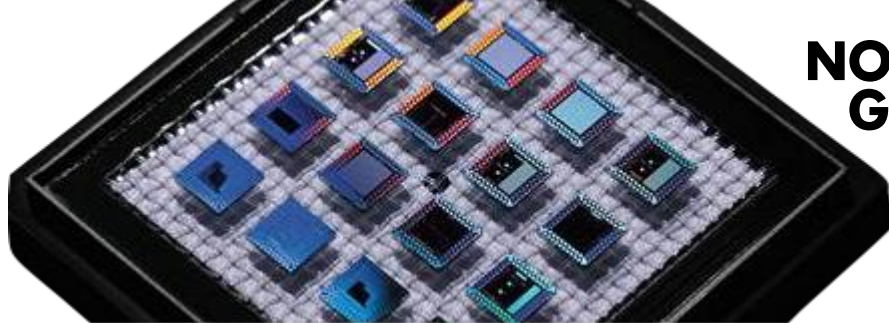
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Absolute Maximum Ratings

Parameter	Value	Unit
Drain Voltage	1.3	V
Gate Voltage Range*	-0.7 to 0.4	V
Drain Current	18	mA
Forward Gate Current	0.12	mA
Reverse Gate Current	-0.3	mA

*Vgd max is 2V

Recommended Operating Conditions

Parameter	Value	Unit
Drain Voltage Range	1.3	V
Gate Voltage Range	-0.7 to 0.3	V
Vd1 Drain Current	13.5	mA
Vd2 Drain Current	6	mA

Electrical Specifications

Parameter	Min	Typ	Max	Unit
Operational Frequency	71		86	GHz
Small Signal S-parameters				
Small Signal Linear Gain	24.5	28.7		dB
Gain Flatness			4.5	dB
Input Return Loss		-11.3	-5	dB
Output Return Loss		-22.5	-13	dB
Noise Figure				
Operation Frequency	75		86	GHz
Noise Figure		2.7	3.2	dB

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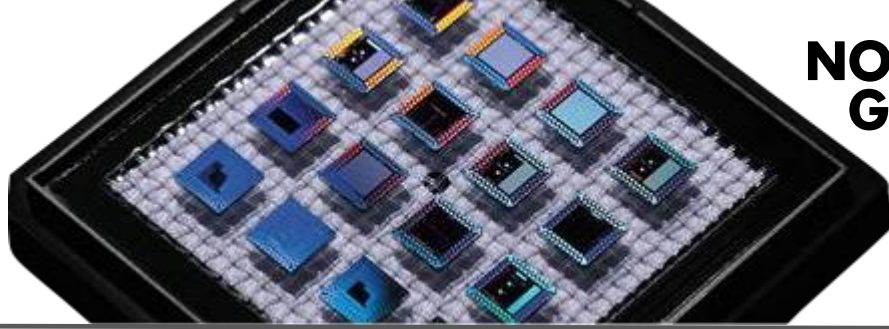
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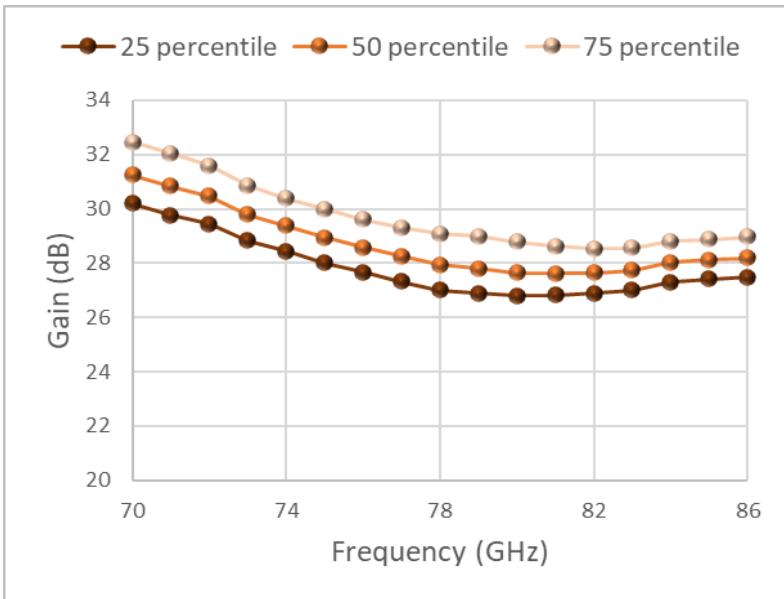


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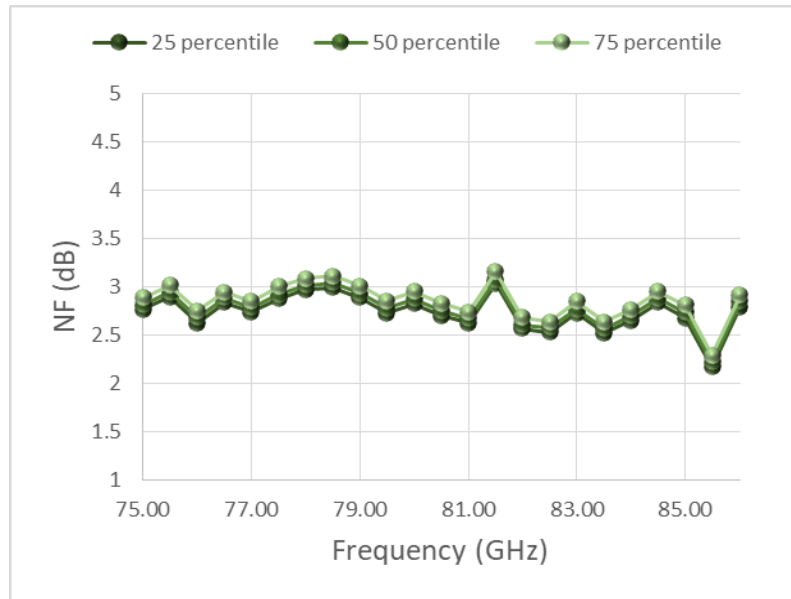
On wafer measured Performance Characteristics (Typical Performance at 25°C)

Vd = 1.3V, Id1 = 13.5 mA, Id2 = 6 mA

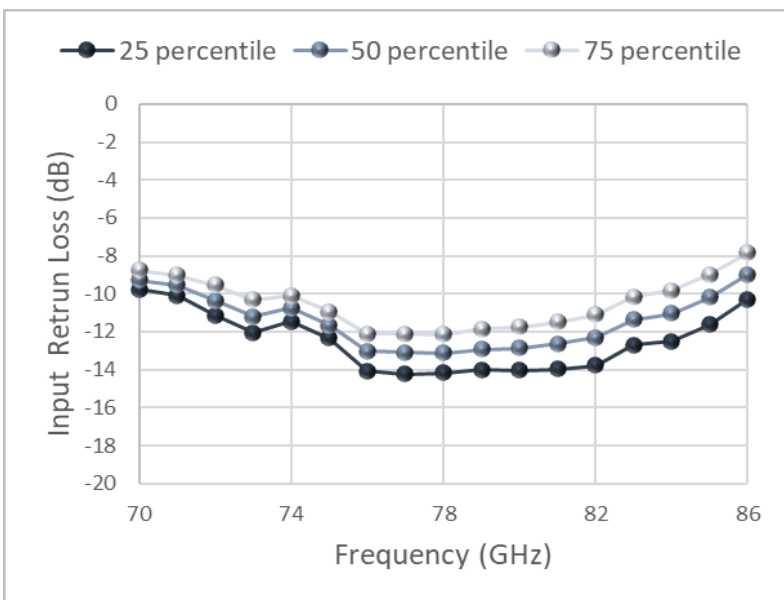
GAIN vs. Frequency



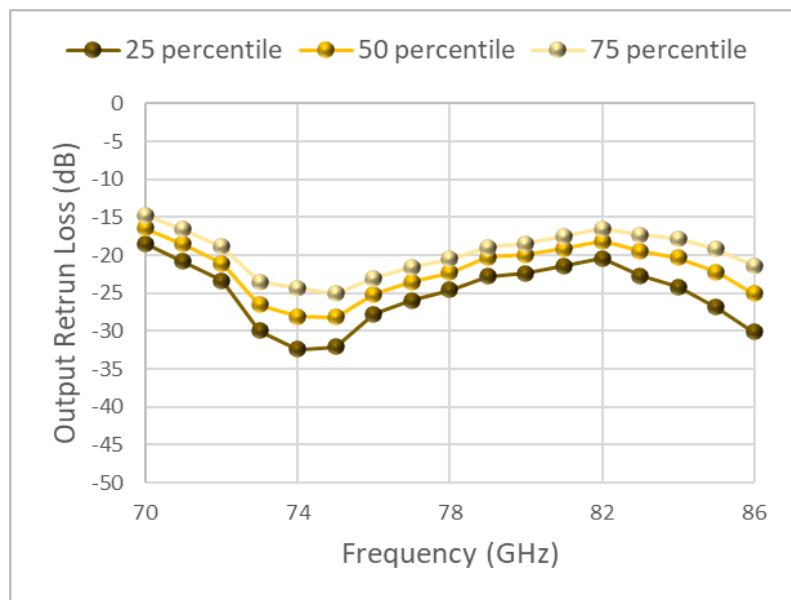
Noise vs. Frequency



Input Return Loss vs. Frequency



Output Return Loss vs. Frequency



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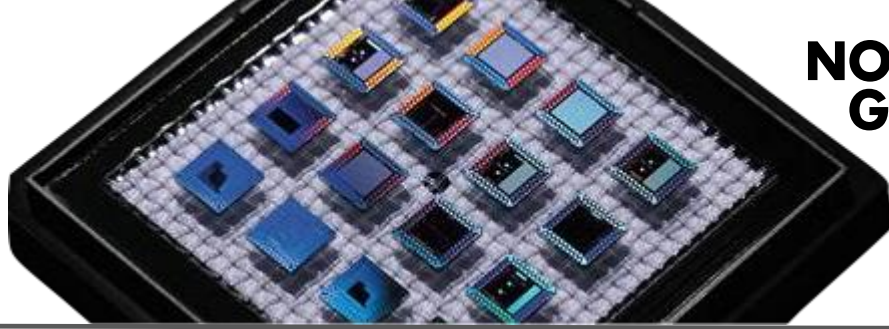
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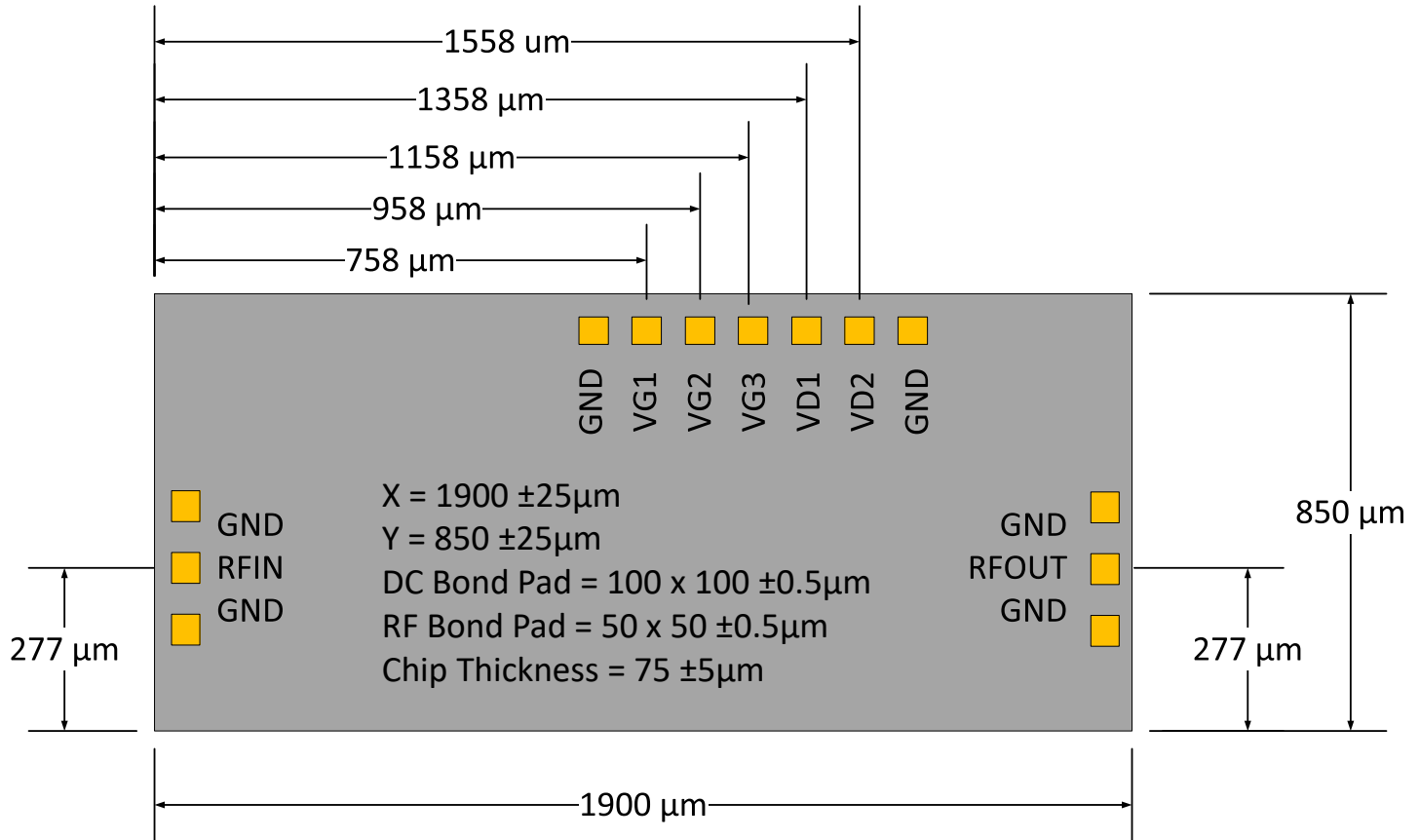
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Die Size and Bond Pad Locations (Not to Scale)



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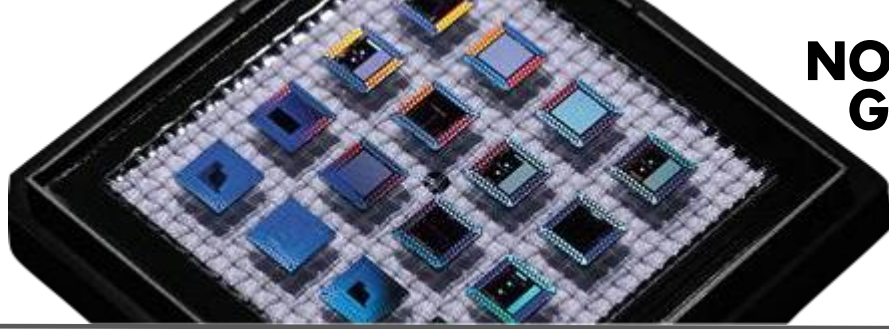
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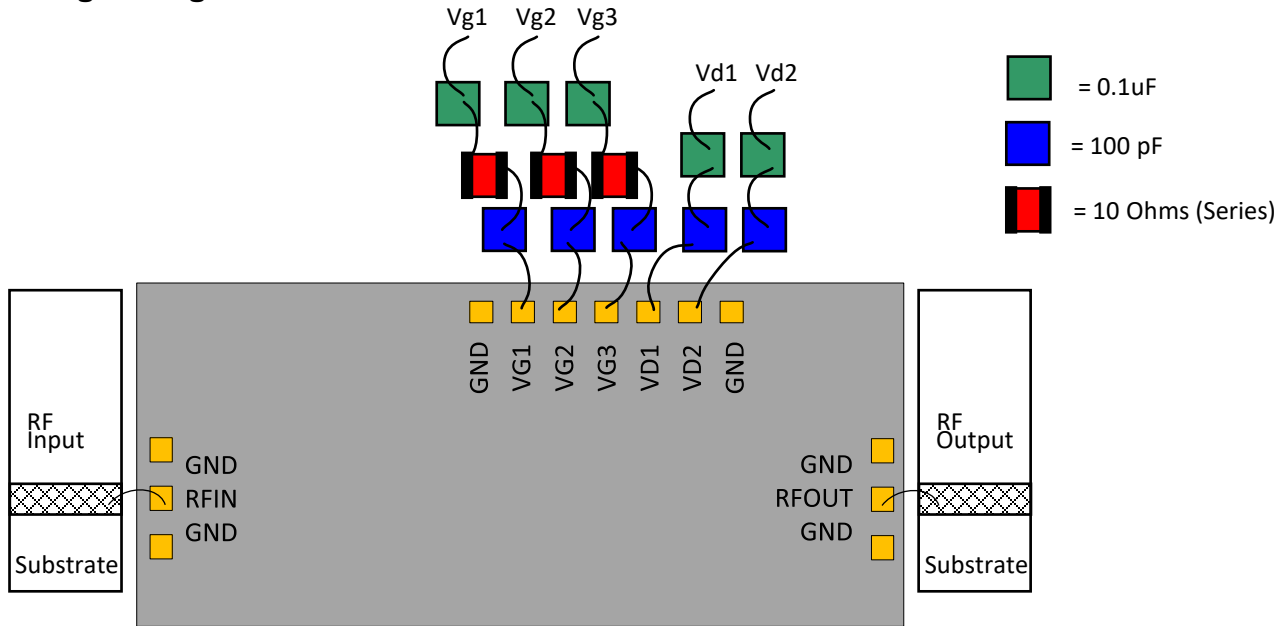
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Suggested Bonding Arrangement



Recommended Assembly Notes

1. Bypass caps should be 100pF (approximately) ceramic (single-layer) placed no further than 30 mils from the amplifier.
2. Best performance obtained from use of <6 mil (long) by 1.5 by 0.5 mil ribbons on input and output

Biasing/De-Biasing Details:

Bias up sequence:

- Set all drain and gate voltages to 0V
- Set $V_{g1} = V_{g2} = V_{g3}$ to -0.7V and check to make sure there is no gate current. High gate current indicates leaky devices.
- Increase V_{d1} and V_{d2} to +0.4V and check to make sure there are no oscillations.
- If no oscillations are evident, increase V_{d1} and V_{d2} voltage to recommended value (1.3V).
- Adjust V_{g1} to realize the desired I_{d1} (4.5mA)
- Adjust V_{g2} to realize the desired I_{d1} (13.5mA)
- Adjust V_{g3} to realize the desired I_{d2} (6mA)

Bias down sequence:

- Set $V_{g1} = V_{g2} = V_{g3}$ to -0.7V
- Set $V_{d1} = V_{d2}$ to 0V
- Set $V_{g1} = V_{g2} = V_{g3}$ to 0V

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